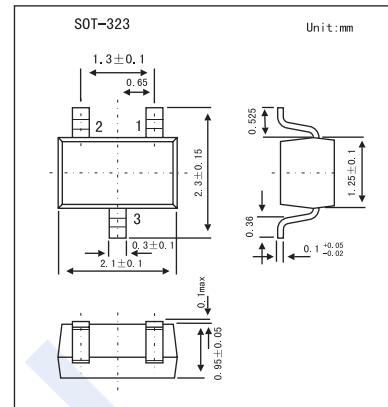
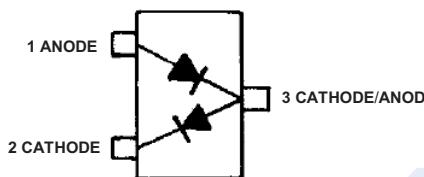


Silicon Epitaxial Schottky Barrier Type**1SS372****■ Features**

- Small package
- Low forward voltage : $V_F = 0.23V$ (typ.) @ $I_F=5mA$

**■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$**

| Parameter | Symbol | Rating | Unit |
|--------------------------------|-----------|-------------|------------------|
| Maximum (Peak) reverse voltage | V_{RM} | 15 | V |
| Reverse voltage | V_R | 10 | V |
| Average forward current | I_o | 100 * | mA |
| Maximum (Peak) forward current | I_{FM} | 200 * | mA |
| Surge current (10ms) | I_{FSM} | 1 * | A |
| Power dissipation | P | 100 | mW |
| Junction temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |
| Operating Temperature Range | T_{opr} | -40 to 100 | $^\circ\text{C}$ |

*Unit Rating .Total Rating= Unit RatingX0.7

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|-------------------|--------|----------------------------|-----|------|------|---------------|
| Forward voltage | V_F | $I_F = 1\text{mA}$ | | 0.18 | | V |
| | | $I_F = 5\text{mA}$ | | 0.23 | 0.30 | |
| | | $I_F = 100\text{mA}$ | | 0.35 | 0.50 | |
| Reverse current | I_R | $V_R = 10\text{V}$ | | | 20 | μA |
| Total capacitance | C_T | $V_R = 0, f = 1\text{MHz}$ | | | 20 | pF |

■ Marking

| | |
|---------|----|
| Marking | N9 |
|---------|----|